

## AMENDMENTS TO THE SPECIFICATION

Please replace Table 2 on page 13 with the following amended Table 2:

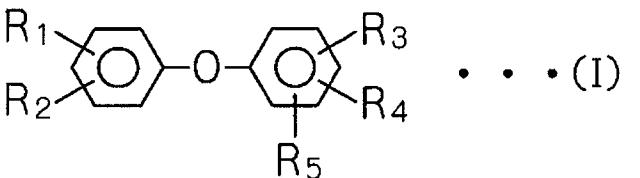
Table 2

	Anionic surfactant		Sulfate ion (ppm)	Methanol (% by mass)	Chloride ion (ppm)	Dimensional controllability
	Kind	Amount (ppm)				
Example 13	<chem>C12H25-C6H4-O-C6H4-SO3NH4-SO3NH4</chem>	3000	500	0.005	2000	B
Example 14	<chem>C12H25-C6H4-O-C6H4-SO3NH4-SO3NH4</chem>	3000	700	0.005	2000	B
Example 15	<chem>C12H25-C6H4-O-C6H4-SO3NH4-SO3NH4</chem>	3000	5000	0.005	2000	B
Example 16	<chem>C12H25-C6H4-O-C6H4-SO3NH4-SO3NH4</chem>	3000	700	0.05	2000	B
Example 17	<chem>C12H25-C6H4-O-C6H4-SO3NH4-SO3NH4</chem>	3000	700	0.3	2000	B
Example 18	<chem>C12H25-C6H4-O-C6H4-SO3NH4-SO3NH4</chem>	3000	700	2.5	2000	B
Example 19	<chem>C5H11-C6H4-O-C6H4-SO3NH4</chem>	1000	700	0.3	300	A
Example 20	<chem>C5H11-C6H4-O-C6H4-SO3NH4</chem>	1000	700	0.3	500	B
Example 21	<chem>C5H11-C6H4-O-C6H4-SO3NH4</chem>	1000	700	0.005	300	B
Example 22	<chem>C5H11-C6H4-O-C6H4-SO3NH4</chem>	1000	700	0.005	500	B
Example 23	<chem>C12H25-C6H4-O-C6H4-SO3NH4-SO3NH4</chem>	20000	700	0.3	300	A
Example 24	<chem>C12H25-C6H4-O-C6H4-SO3NH4-SO3NH4</chem>	50000	700	0.3	300	B
Example 22 25	<chem>C12H25-C6H4-O-C6H4-SO3NH4-SO3NH4</chem>	3000	700	0.3	300	B

## AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A developer composition for resists, comprising an organic quaternary ammonium base as a main component, said organic quaternary ammonium base having a lower alkyl group or a lower hydroxyalkyl group, wherein the lower alkyl group or lower hydroxyalkyl group has 1 to 5 carbon atoms, wherein said organic quaternary ammonium base is present in an amount from 0.1 to 10% by mass;

said developer further comprising an anionic surfactant in an amount from 500 1,000 to 400,000 50,000 ppm represented by the following general formula (I):



wherein at least one of R<sub>1</sub> and R<sub>2</sub> represents an alkyl or alkoxy group having 5 to 18 carbon atoms and the other one represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one of R<sub>3</sub>, R<sub>4</sub> and R<sub>5</sub> represents an ammonium sulfonate group or a sulfonic acid-substituted ammonium group and the others represent a hydrogen atom, an ammonium sulfonate group or a sulfonic acid-substituted ammonium group;

SO<sub>4</sub><sup>2-</sup> in an amount from 40 50 to 10,000 5,000 ppm; and

a lower alcohol in an amount from 0.05 0.005 to 2.5% by mass.

2. (Canceled)

3. (Canceled)

4. (Previously presented) A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 1 to form a resist pattern.

5. (Previously presented) The developer composition for resists according to claim 1, wherein said lower alcohol has 1 to 5 carbon atoms.

6. (Previously presented) The developer composition for resists according to claim 5, wherein the lower alcohol is ethanol or methanol.

7. (**Previously presented**) The developer composition for resists according to claim 1, wherein the amount of said organic quaternary ammonium base is 0.1 to 10% by mass based on the developer composition for resists.

8. (**Currently amended**) The developer composition for resists according to claim 1, further comprising a halogen ion in an amount of 1,000 ppm or less 300 to 2,000 ppm.

9. (**Previously presented**) The developer composition for resists according to claim 8, wherein the amount of the halogen ion is from 300 to 1,000 ppm.

10. (**New**) The developer composition for resists according to claim 1, wherein said organic quaternary ammonium base is in an amount from 2 to 5% by mass.

11. (**New**) The developer composition for resists according to claim 1, wherein said  $\text{SO}_4^{2-}$  is in an amount from 100 to 1,000 ppm.

12. (**New**) The developer composition for resists according to claim 1, wherein said lower alcohol is in an amount from 0.1 to 1% by mass.

13. (**New**) The developer composition for resists according to claim 8, wherein said halogen ion is in an amount of 1,000 ppm or less.